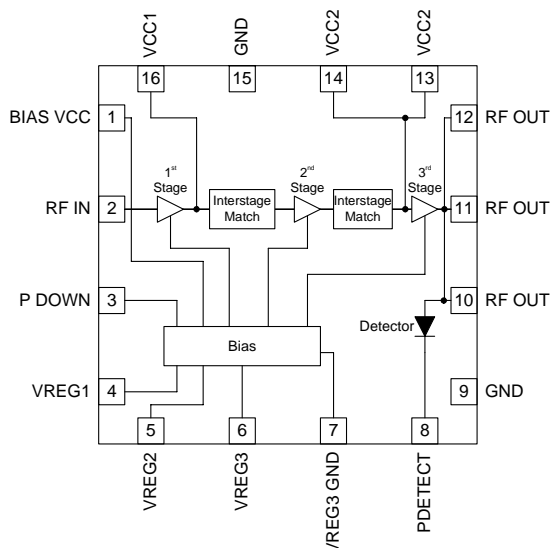


**Features**

- Single 3.3V or 5.0V Power Supply
- 34dB Small Signal Gain (typ.)
- <2% EVM (RMS) 54Mbps @ +26dBm
- Separate Power Detect/Power Down Pins
- Multiple Frequency Ranges

Applications

- 802.11b/g/n Access Points
- PCS Communication Systems
- 2.4GHz ISM Band Applications
- Commercial and Consumer Systems
- WiBro 2.3GHz to 2.4GHz Band Applications
- WiMAX 2.5GHz to 2.7GHz Band Applications



Functional Block Diagram

Product Description

The RF5263 is a linear power amplifier IC designed specifically for medium power applications. The device is manufactured on an advanced InGaP Heterojunction Bipolar Transistor (HBT) process, and has been designed for use as the final RF amplifier in 802.11g/n access point transmitters. The device is provided in a 4mmx4mm, 16-pin, leadless chip carrier with a backside ground. The RF5263 is designed to maintain linearity over a wide range of supply voltages and power outputs.

Ordering Information

RF5263	3.3V to 5.0V, 2.5GHz Linear Power Amplifier, Matte-Sn (Pb-free) Finish
RF5263WLPC-410	2.4-2.5GHz WLAN Fully Assembled Eval PCB
RF5263WBPC-410	2.3-2.4GHz WiBro Fully Assembled Eval PCB
RF5263WMPCK-410	2.5-2.7GHz WiMAX Fully Assembled Eval PCB

Optimum Technology Matching® Applied

- | | | | |
|---|--------------------------------------|-------------------------------------|-----------------------------------|
| <input type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS | <input type="checkbox"/> Si CMOS | |
| <input checked="" type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si BJT | |

**Please contact
RFMD Technical Support
at (336) 678-5570
for more information.**